

UP05C8GG

Silicon NPN epitaxial planar type (Tr)
 Silicon epitaxial planar type (CCD load device)

For CCD output circuits

■ Features

- Two elements incorporated into one package (Tr + CCD load device)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

■ Basic Part Number

- 2SC3932G + CCD load device

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr	Collector-base voltage (Emitter open)	V_{CBO}	30	V
	Collector-emitter voltage (Base open)	V_{CEO}	20	V
	Emitter-base voltage (Collector open)	V_{EBO}	3	V
	Collector current	I_C	50	mA
CCD load device	Limiting element voltage	V_{max}	40	V
	Limiting element current	I_{max}	10	mA
Overall	Total power dissipation*	P_T	125	mW
	Junction temperature	T_j	125	$^\circ\text{C}$
	Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note) * : Measuring on substrate at 17 mm × 10 mm × 1 mm

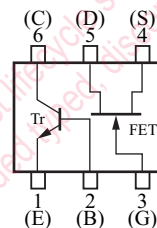
■ Package

- Code
SSMini6-F2
- Pin Name

1: Emitter	4: Source
2: Base	5: Drain
3: Gate	6: Collector

■ Marking Symbol: 4V

■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	30			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	3			V
Base-emitter voltage	V_{BE}	$V_{CE} = 10 \text{V}, I_C = 2 \text{mA}$		720		mV
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{V}, I_C = 2 \text{mA}$	25		250	—
Transition frequency *	f_T	$V_{CB} = 10 \text{V}, I_E = -15 \text{mA}, f = 200 \text{MHz}$	800		1200	MHz
Power gain	PG	$V_{CB} = 10 \text{V}, I_E = -1 \text{mA}, f = 100 \text{MHz}$		20		dB

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

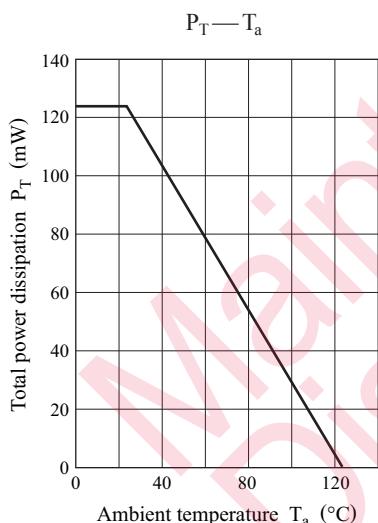
*: Pulse measurement

• CCD Load Device

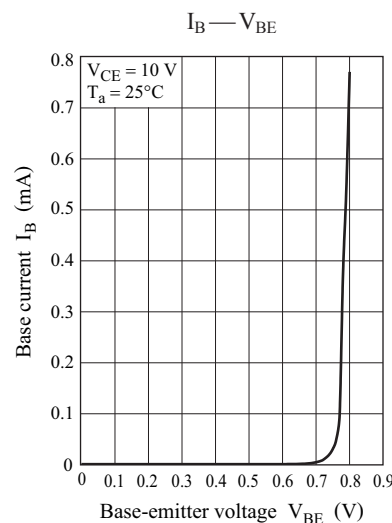
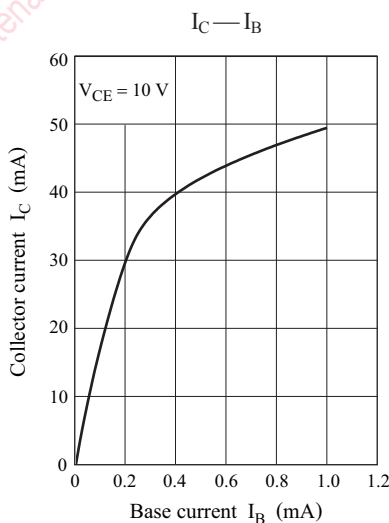
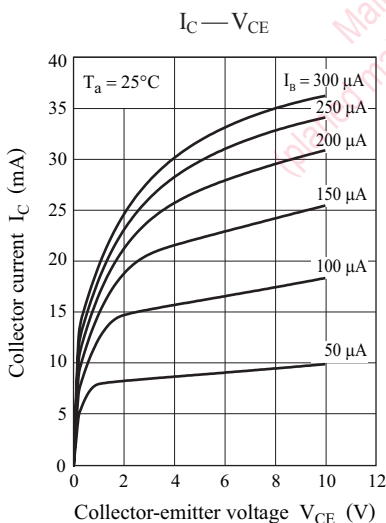
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Pinch off current	I_P	$V_{DS} = 10 \text{V}, V_G = 0$	3.5		5.5	mA
Output impedance	Z_O	$V_{DS} = 10 \text{V}, V_G = 0$		0.05		$\text{M}\Omega$

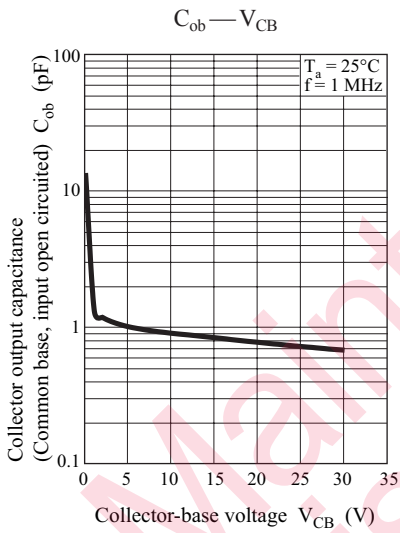
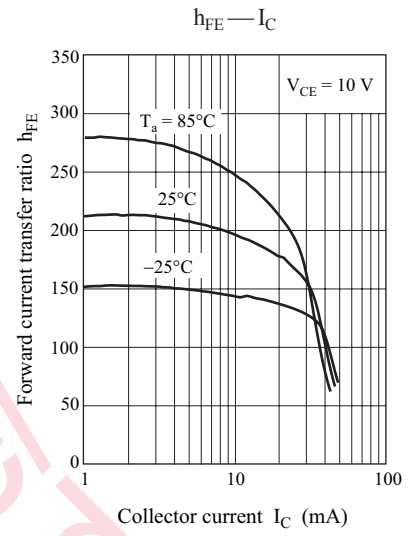
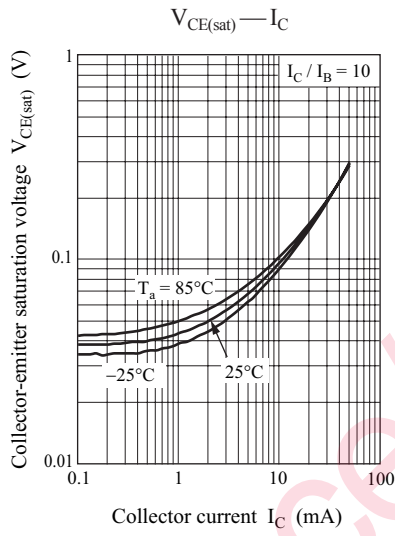
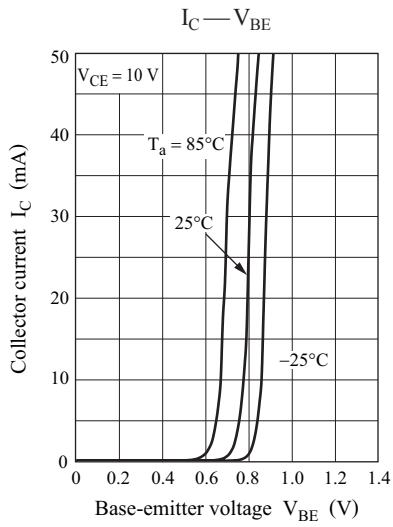
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Common characteristics chart

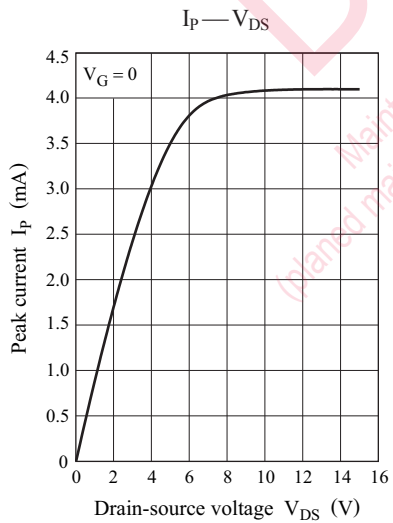


Characteristics charts of Tr



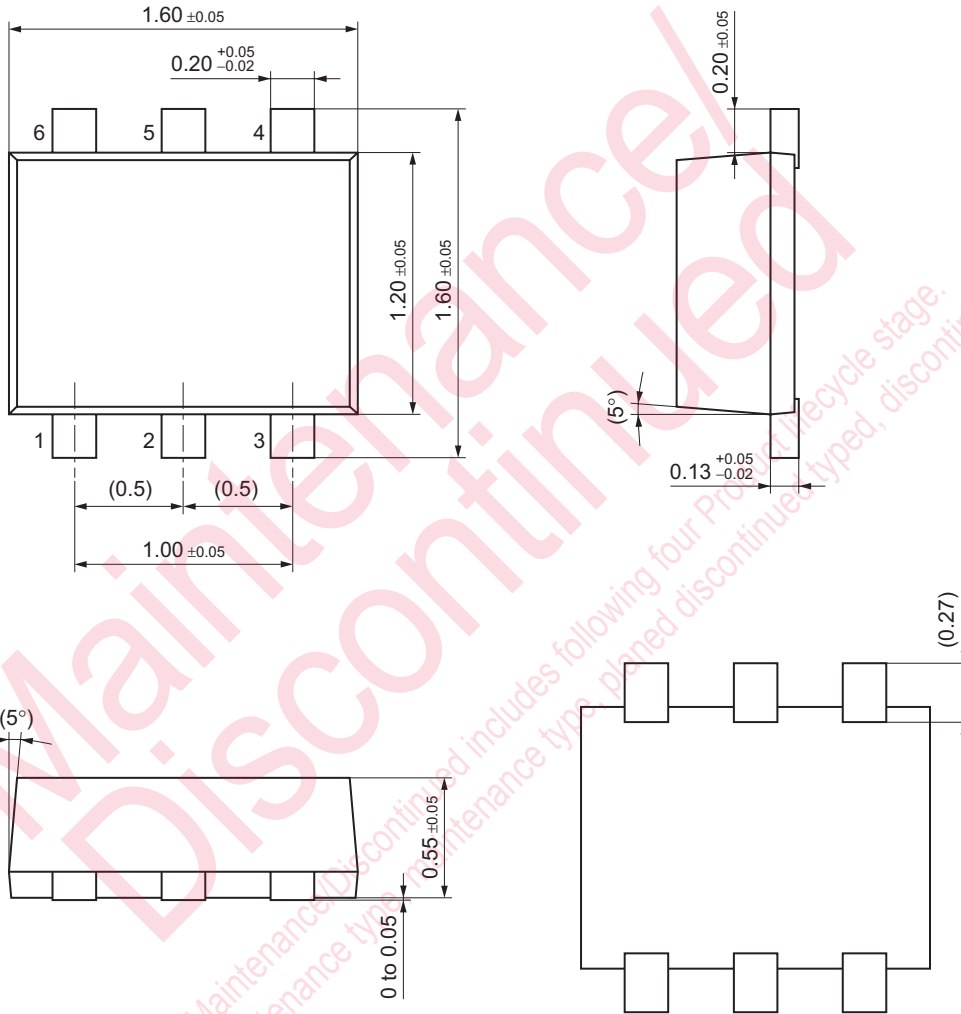


Characteristics charts of CCD load device



SSMini6-F2

Unit: mm



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